



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of: **IRINO, Kiyoshi**

Serial No.: **09/428,052**

Filed: **October 27, 1999**

Group Art Unit: **2815**

Examiner: **Jose R. Diaz**

P.T.O. Confirmation No.: **4139**

For: **METHOD FOR FABRICATING A SEMICONDUCTOR DEVICE CONTAINING NITROGEN IN A GATE OXIDE FILM (As Amended)**

AMENDMENT UNDER 37 CFR §1.111

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

May 27, 2003

Sir:

In response to the Office Action dated **February 27, 2003**, please amend the above-identified application as follows:

IN THE CLAIMS:

Please cancel claims 11 and 12 without prejudice or disclaimer.

Please amend claim 10 as follows:

10. (Seven Times Amended) A method of fabricating a semiconductor device, comprising the steps of:

forming a gate oxide film on a substrate by a thermal oxide film;

forming a gate electrode pattern on said gate oxide film such that said gate electrode pattern is in direct contact with said gate oxide film;

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